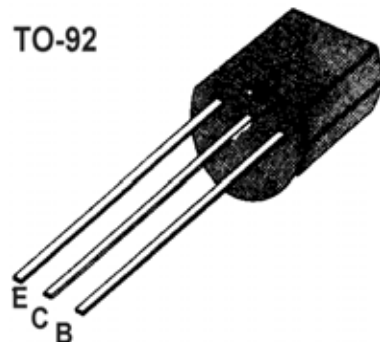


APPLICATION: GENERAL PURPOSE APPLICATION.

MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _c	-150	mA
Collector Power Dissipation	P _c	400	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Common Emitter DC Current Gain	h _{FE}	70		400		V _{CE} = -6V, I _c = -2mA
Collector Cut-off Current	I _{CB0}			-0.1	μA	V _{CB} = -50V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.1	μA	V _{EB} = -5V, I _c =0
Collector-Base Breakdown Voltage	BV _{CB0}	-50			V	I _c = -0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-50			V	I _c = -1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	5			V	I _E = -0.1mA, I _c =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-0.1	-0.3	V	I _c = -100mA, I _B = -10mA
Gain bandwidth product	f _r	80			MHz	I _c = -1mA, V _{CE} = -10V
Common Base Output Capacitance	C _{ob}		4	7	PF	V _{CB} = -10V, I _E =0, f= 1MHz
Noise Figure	N _F		1	10	dB	V _{CE} = -6V, I _c = -0.1mA, f= 1KHz, R _g =10KΩ

h_{FE} Classification

Classification	O	Y	GR
h _{FE}	70~140	120~240	200~400